

Three Phase Rectifier Bridge

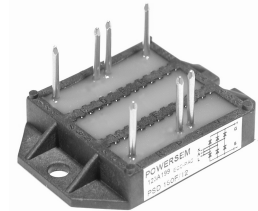
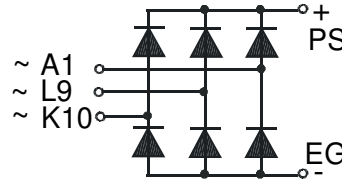
PSD 150F

with fast Recovery Epitaxial Diode (FRED)

$I_{dAV} = 130 \text{ A}$
 $V_{RRM} = 800 - 1200 \text{ V}$
 $t_{rr} = 40 \text{ ns}$

Preliminary Data Sheet

V_{RSM} V_{DSM} (V)	V_{RRM} V_{DRM} (V)	Type
800	800	PSD 150F/08
1200	1200	PSD 150F/12



Symbol	Test Conditions	Maximum Ratings
I_{dAV}^*	$T_C = 75 \text{ }^\circ\text{C}$, (per module)	130 A
I_{FSM}	$T_{VJ} = 45 \text{ }^\circ\text{C}$ t = 10 ms (50 Hz), sine	500 A
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	550 A
	$T_{VJ} = T_{VJM}$ t = 10 ms (50 Hz), sine	450 A
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	500 A
$\int i^2 dt$	$T_{VJ} = 45 \text{ }^\circ\text{C}$ t = 10 ms (50 Hz), sine	1250 A ² s
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	1250 A ² s
	$T_{VJ} = T_{VJM}$ t = 10 ms (50 Hz), sine	1010 A ² s
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	1040 A ² s
T_{VJ}		-40... + 150 $^\circ\text{C}$
T_{VJM}		150 $^\circ\text{C}$
T_{stg}		-40... + 125 $^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS t = 1 min	3000 V~
	$I_{ISOL} \leq 1 \text{ mA}$ t = 1 s	3600 V~
M_d	Mounting torque (M4)	1.5 - 2.0 Nm
		14 - 18 lb.in.
Weight	typ.	22 g

Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered, E 148688

Applications

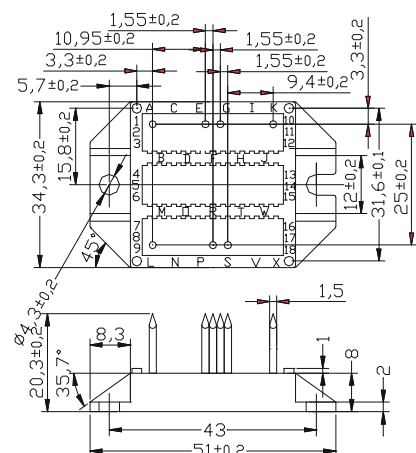
- Supplies for DC power equipment
- Input and output rectifier for high frequency
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Low noise switching
- Small and light weight

Package style and outline

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Value
I_R	$V_R = V_{RRM}, T_{VJ} = T_{VJM}$	$\leq 2.5 \text{ mA}$
	$V_R = V_{RRM}, T_{VJ} = 25 \text{ }^\circ\text{C}$	$\leq 0.65 \text{ mA}$
V_F	$I_F = 60 \text{ A}, T_{VJ} = 25 \text{ }^\circ\text{C}$	$\leq 2.75 \text{ V}$
V_{TO}	For power-loss calculations only	1.12 V
r_T		5.7 m Ω
R_{thJC}	per diode; DC	0.85 K/W
	per module	0.14 K/W
R_{thJK}	per diode; DC	1.0 K/W
	per module	0.16 K/W
I_{RM}	$I_F = 130 \text{ A}; -di_F/dt = 100 \text{ A}/\mu\text{s}; V_R = 100 \text{ V}$ $L = 0.05 \text{ mH}; T_{VJ} = 100 \text{ }^\circ\text{C}$	typ. 7.8 A
t_{rr}	$I_F = 1 \text{ A}; -di_F/dt = 200 \text{ A}/\mu\text{s}; V_R = 30 \text{ V};$ $T_{VJ} = 25 \text{ }^\circ\text{C}$	typ. 40 ns
d_s	Creeping distance on surface	11.2 mm
d_A	Creeping distance in air	9.45 mm
a	Max. allowable acceleration	50 m/s ²

Data according to IEC 60747 refer to a single diode unless otherwise stated
 *- for resistive load at bridge output